

August 2005

LMH6723/LMH6724/LMH6725 Single/Dual/Quad 370 MHz 1 mA Current Feedback Operational Amplifier

General Description

The LMH6723/LMH6724/LMH6725 provides a 260 MHz small signal bandwidth at a gain of +2 V/V and a 600 V/µs slew rate while consuming only 1 mA from ±5V supplies.

The LMH6723/LMH6724/LMH6725 supports video applications with its 0.03% and 0.11° differential gain and phase for NTSC and PAL video signals. The LMH6723/LMH6724/LMH6725 also offers a flat gain response of 0.1 dB to 100 MHz. Additionally, the LMH6723/LMH6724/LMH6725 can deliver 110 mA of linear output current. This level of performance, as well as a wide supply range of 4.5 to 12V, makes the LMH6723/LMH6724/LMH6725 an ideal op amp for a variety of portable applications. The LMH6723/LMH6724/LMH6725's small packages (TSSOP, SOIC & SOT23), low power requirement and high performance allow the LMH6723/LMH6724/LMH6725 to serve a wide variety of portable applications.

The LMH6723/LMH6724/LMH6725 is manufactured in National's VIP10™ complimentary bipolar process.

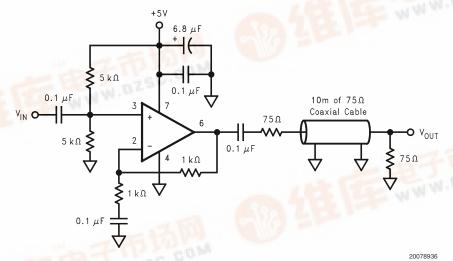
Features

- Large signal bandwidth and slew rate 100% tested
- 370 MHz bandwidth ($A_V = 1$, $V_{OUT} = 0.5 V_{PP}$) -3 dB BW
- 260 MHz ($A_V = +2 \text{ V/V}, V_{OUT} = 0.5 V_{PP}$) -3 dB BW
- 1 mA supply current
- 110 mA linear output current
- 0.03%, 0.11° differential gain, phase
- 0.1 dB gain flatness to 100 MHz
- Fast slew rate: 600 V/µs
- Unity gain stable
- Single supply range of 4.5 to 12V
- Improved replacement for CLC450, CLC452, (LMH6723)

Applications

- Line driver
- Portable video
- A/D driver
- Portable DVD

Typical Application



Single Supply Cable Driver

PDF
VIP10™ s a trademark of National Semiconductor Corporation

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

 V_{CC} (V⁺ - V⁻) $\pm 6.75V$ I_{OUT} 120 mA (Note 3) Common Mode Input Voltage $\pm V_{CC}$ Maximum Junction Temperature $+150^{\circ}C$ Storage Temperature Range $-65^{\circ}C$ to $+150^{\circ}C$

Soldering Information

Infrared or Convection (20 sec) 235°C Wave Soldering (10 sec) 260°C

ESD Tolerance (Note 4)

Human Body Model 2000V Machine Model (Note 4) 200V

Operating Ratings (Note 3)

Thermal Resistance

 $\begin{array}{ccc} Package & & & & & \\ 8\text{-Pin SOIC} & & & & 166\,^{\circ}\text{C/W} \\ 5\text{-Pin SOT23} & & & 230\,^{\circ}\text{C/W} \\ 14\text{-Pin SOIC} & & & 130\,^{\circ}\text{C/W} \\ 14\text{-Pin TSSOP} & & 160\,^{\circ}\text{C/W} \\ Operating Temperature Range & & -40\,^{\circ}\text{C to } +85\,^{\circ}\text{C} \\ Nominal Supply Voltage & & 4.5V to 12V \\ \end{array}$

±5V Electrical Characteristics

Unless otherwise specified, A_V = +2, R_F = 1200 Ω , R_L = 100 Ω . **Boldface** limits apply at temperature extremes. (Note 2)

Symbol	Parameter	Conditions		Min	Тур	Max	Units	
Frequency	Domain Response				•		•	
SSBW	-3 dB Bandwidth Small Signal	$V_{OUT} = 0.5 V_{PP}$			260		MHz	
LSBW	-3dB Bandwidth Large Signal	$V_{OUT} = 4.0 V_{PP}$	LMH6723	90	110			
			LMH6724	85	95		MHz	
			LMH6725					
UGBW	-3 dB Bandwidth Unity Gain	$V_{OUT} = .2 V_{PP} A_V = 1 V/V$			370		MHz	
.1dB BW	.1 dB Bandwidth	$V_{OUT} = 0.5 V_{PP}$			100		MHz	
DG	Differential Gain	$R_L = 150\Omega, 4.43 \text{ MHz}$			0.03		%	
DP	Differential Phase	$R_L = 150\Omega$, 4.43 MHz			0.11		deg	
Time Dom	ain Response							
TRS	Rise and Fall Time	4V Step			2.5		ns	
TSS	Settling Time to 0.05%	2V Step			30		ns	
SR	Slew Rate	4V Step		500	600		V/µs	
Distortion	and Noise Response				•		•	
HD2	2 nd Harmonic Distortion	2 V _{PP} , 5 MHz			-65		dBc	
HD3	3 rd Harmonic Distortion	2 V _{PP} , 5 MHz			-63		dBc	
Equivalen	t Input Noise				•		•	
VN	Non-Inverting Voltage Noise	>1 MHz			4.3		nV/ √H	
NICN	Inverting Current Noise	>1 MHz			6		pA/ √H	
ICN	Non-Inverting Current Noise	>1 MHz			6		pA/ √H	
Static, DC	Performance	•	•		•		<u>'</u>	
V _{IO}	Input Offset Voltage				1	±3	\/	
						±3.7	mV	
I _{BN}	Input Bias Current	Non-Inverting			-2	±4		
						±5	μA	
I _{BI}	Input Bias Current	Inverting			0.4	±4	μA	
						±5	μΛ	
PSRR	Power Supply Rejection Ratio	DC, 1V Step	LMH6723	59	64			
				57				
			LMH6724	59	64		dB	
				55			1 -	
			LMH6725	59	64			
				56				

±5V Electrical Characteristics (Continued)

Unless otherwise specified, A_V = +2, R_F = 1200 Ω , R_L = 100 Ω . **Boldface** limits apply at temperature extremes. (Note 2)

Symbol	Parameter	Conditions		Min	Тур	Max	Units
CMRR	Common Mode Rejection Ratio	DC, 1V Step	LMH6723	57 55	60		
			LMH6724	57 53	60		dB
			LMH6725	57 54	60		-
I _{CC}	Supply Current (per amplifier)	R _L = ∞			1	1.2 1.4	mA
Miscelland	eous Performance						•
R _{IN+}	Input Resistance	Non-Inverting			100		kΩ
R _{IN-}	Input Resistance (Output Resistance of Input Buffer)	Inverting			500		Ω
C _{IN}	Input Capacitance	Non-Inverting			1.5		pF
R _{OUT}	Output Resistance	Closed Loop			0.01		Ω
V _O	Output Voltage Range	R _L = ∞	LMH6723	±4 ±3.9	±4.1		.,
			LMH6724 LMH6725	±4 ±3.85	±4.1		V
V _{OL}	Output Voltage Range, High	$R_L = 100\Omega$		3.6 3.5	3.7		V
	Output Voltage Range, Low	$R_L = 100\Omega$		-3.25 -3.1	-3.45		V
CMVR	Input Voltage Range	Common Mode, CMRR > 50 dB		±4.0			V
Io	Output Current	Sourcing, V _{OUT} = 0		95 70	110		m A
		Sinking, V _{OUT} = 0		-80 -70	110		- mA

±2.5V Electrical Characteristics

Unless otherwise specified, $A_V = +2$, $R_F = 1200\Omega$, $R_L = 100\Omega$. **Boldface** limits apply at temperature extremes. (Note 2)

Symbol	Parameter	Condition	ons	Min	Тур	Max	Units
Frequency	Domain Response	•					
SSBW	-3 dB Bandwidth Small Signal	$V_{OUT} = 0.5 V_{PP}$			210		MHz
LSBW	-3 dB Bandwidth Large Signal	$V_{OUT} = 2.0 V_{PP}$	LMH6723	95	125		
			LMH6724				MHz
			LMH6725	90	100		1
UGBW	-3 dB Bandwidth Unity Gain	$V_{OUT} = 0.5 V_{PP}, A_V =$	1 V/V		290		MHz
.1dB BW	.1 dB Bandwidth	$V_{OUT} = 0.5 V_{PP}$			100		MHz
DG	Differential Gain	$R_L = 150\Omega, 4.43 \text{ MHz}$	$R_L = 150\Omega$, 4.43 MHz		.03		%
DP	Differential Phase	$R_L = 150\Omega$, 4.43 MHz			0.1		deg
Time Dom	ain Response	1					
TRS	Rise and Fall Time	2V Step			4		ns
SR	Slew Rate	2V Step		275	400		V/µs
Distortion	and Noise Response						
HD2	2 nd Harmonic Distortion	2 V _{PP} , 5 MHz			-67		dBc
HD3	3 rd Harmonic Distortion	2 V _{PP} , 5 MHz			-67		dBc
Equivalen	t Input Noise	•					1
VN	Non-Inverting Voltage	>1 MHz			4.3		nV/ √Hz

 $\pm 2.5V$ Electrical Characteristics (Continued) Unless otherwise specified, A_V = +2, R_F = 1200 Ω , R_L = 100 Ω . Boldface limits apply at temperature extremes. (Note 2)

Symbol	Parameter	Conditions		Min	Тур	Max	Units
NICN	Inverting Current	>1MHz			6		pA/ √Hz
ICN	Non-Inverting Current	>1MHz			6		pA/ √Hz
Static, DC	Performance						
V_{IO}	Input Offset Voltage				-0.5	±3 ±3.4	mV
I _{BN}	Input Bias Current	Non-Inverting			-2.7	±4 ±5	μА
I _{BI}	Input Bias Current	Inverting			-0.7	±4 ±5	μА
PSRR	Power Supply Rejection Ratio	DC, 0.5V Step	LMH6723	59 57	62		
			LMH6724	58 55	62		dB
			LMH6725	59 56	62		
CMRR	Common Mode Rejection Ratio	DC, 0.5V Step	LMH6723	57 53	59		
			LMH6724	55 52	59		dB
			LMH6725	57 52	59		
I _{CC}	Supply Current (per amplifier)	R _L = ∞	1		.9	1.1 1.3	mA
Miscellan	eous Performance						'
R _{IN+}	Input Resistance	Non-Inverting			100		kΩ
R_{IN-}	Input Resistance (Output Resistance of Input	Inverting			500		Ω
	Buffer)				I I	1	1
C _{IN}	Buffer) Input Capacitance	Non-Inverting			1.5		pF
	<u>'</u>	Non-Inverting Closed Loop			1.5		pF Ω
C _{IN} R _{OUT} V _O	Input Capacitance			±1.55 ±1.4			-
R _{OUT}	Input Capacitance Output Resistance	Closed Loop	LMH6723		.02		Ω V
R _{OUT}	Input Capacitance Output Resistance Output Voltage Range	Closed Loop R _L = ∞	LMH6723 LMH6724 LMH6725	±1.4 1.35	.02 ±1.65		Ω
R _{OUT}	Input Capacitance Output Resistance Output Voltage Range	Closed Loop R _L = ∞	LMH6724	±1.4 1.35 1.27 1.35	.02 ±1.65		Ω V
R _{OUT}	Input Capacitance Output Resistance Output Voltage Range Output Voltage Range, High	Closed Loop $R_L = \infty$ $R_L = 100\Omega$	LMH6724 LMH6725	±1.4 1.35 1.27 1.35 1.26 -1.25	.02 ±1.65 1.45		Ω V
R _{OUT}	Input Capacitance Output Resistance Output Voltage Range Output Voltage Range, High	Closed Loop $R_L = \infty$ $R_L = 100\Omega$	LMH6724 LMH6725 LMH6723 LMH6724 LMH6725	±1.4 1.35 1.27 1.35 1.26 -1.25 -1.15	.02 ±1.65 1.45 1.45 -1.38		Ω V
R _{OUT} V _O	Input Capacitance Output Resistance Output Voltage Range Output Voltage Range, High Output Voltage Range, Low	Closed Loop $R_L = \infty$ $R_L = 100\Omega$ $R_L = 100\Omega$	LMH6724 LMH6725 LMH6723 LMH6724 LMH6725	±1.4 1.35 1.27 1.35 1.26 -1.25 -1.15 -1.25	.02 ±1.65 1.45 1.45 -1.38		ν ν - ν

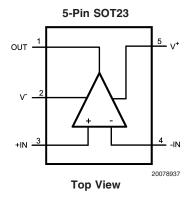
Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not guaranteed. For guaranteed specifications, see the Electrical Characteristics tables.

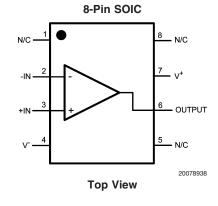
Note 2: Electrical Table values apply only for factory testing conditions at the temperature indicated. Factory testing conditions result in very limited self-heating of the device such that $T_J = T_A$. No guarantee of parametric performance is indicated in the electrical tables under conditions of internal self heating where $T_J > T_A$. See Applications Section for information on temperature derating of this device. Min/Max ratings are based on product characterization and simulation. Individual parameters are tested as noted.

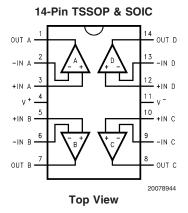
Note 3: The maximum continuous output current (I_{OUT}) is determined by device power dissipation limitations. See the Power Dissipation section of the Application Section for more details.

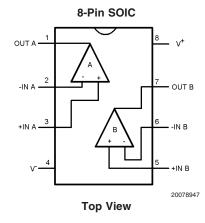
Note 4: Human Body Model, 1.5 k Ω in series with 100 pF. Machine Model, 0Ω In series with 200 pF.

Connection Diagrams







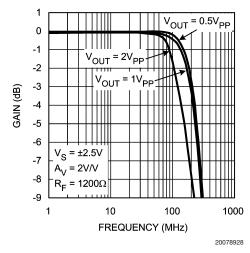


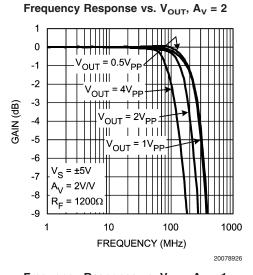
Ordering Information

Package	Part Number Package Marking Transport		Transport Media	NSC Drawing	
5-Pin SOT23	LMH6723MF	AB1A	1k Units Tape and Reel	MF05A	
5-FIII 30123	LMH6723MFX	ADIA	3k Units Tape and Reel	WIFUSA	
8-Pin SOIC	LMH6723MA	LMH6723MA	95 Units/Rail	M08A	
6-7111 3010	LMH6723MAX	LIVINO723IVIA	2.5k Units Tape and Reel	IVIOOA	
8-Pin SOIC	LMH6724MA	LMH6724MA	95 Units/Rail	M08A	
6-7111 3010	LMH6724MAX	LIVINO724IVIA	2.5k Units Tape and Reel	IVIOOA	
14-Pin SOIC	LMH6725MA	LMH6725MA	55 Units/Rail	M14A	
14-7111 3010	LMH6725MAX	LIVINO725IVIA	2.5k Units Tape and Reel	IVIT4A	
14-Pin TSSOP	LMH6725MT	LMH6725MT	94 Units/Rail		
14-5111 13305	LMH6725MTX	LIVII 10723IVI I	2.5k Units Tape and Reel	MTC14	

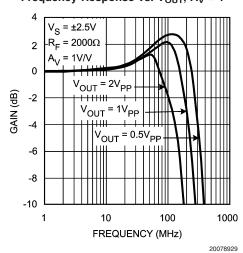
Typical Performance Characteristics $A_V = 2$, $R_F = 1200\Omega$, $R_L = 100\Omega$, unless otherwise specified.

Frequency Response vs. V_{OUT} , $A_V = 2$

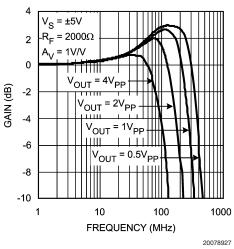




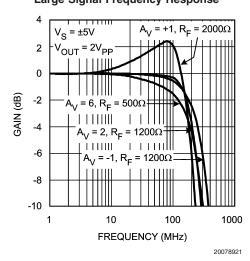
Frequency Response vs. V_{OUT} , $A_V = 1$



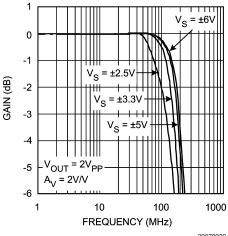
Frequency Response vs. V_{OUT} , $A_V = 1$



Large Signal Frequency Response



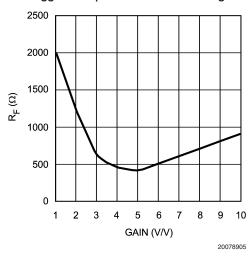
Frequency Response vs. Supply Voltage



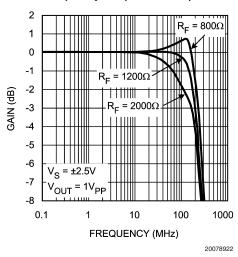
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Typical Performance Characteristics $A_V = 2$, $R_F = 1200\Omega$, $R_L = 100\Omega$, unless otherwise specified. (Continued)

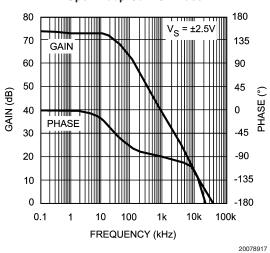
Suggested R_F vs. Gain Non-Inverting



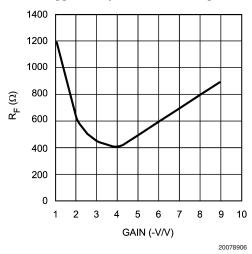
Frequency Response vs. R_F



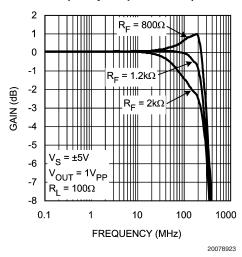
Open Loop Gain & Phase



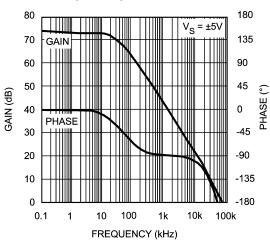
Suggested R_F vs. Gain Inverting



Frequency Response vs. R_F

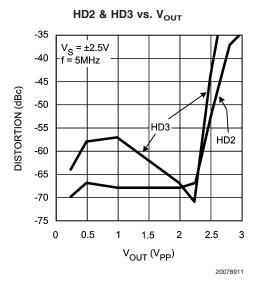


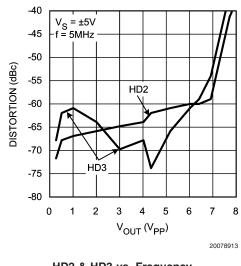
Open Loop Gain & Phase



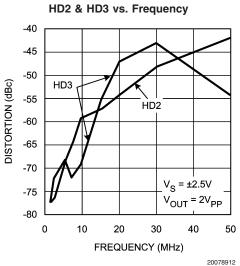
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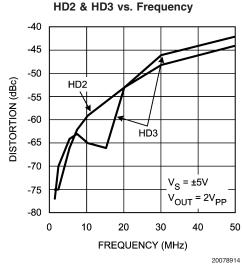
Typical Performance Characteristics $A_V = 2$, $R_F = 1200\Omega$, $R_L = 100\Omega$, unless otherwise specified. (Continued)

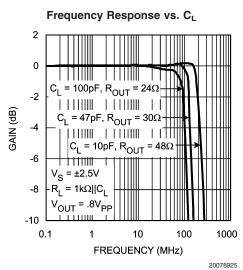


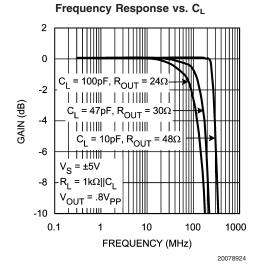


HD2 & HD3 vs. V_{OUT}



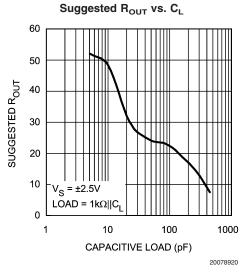






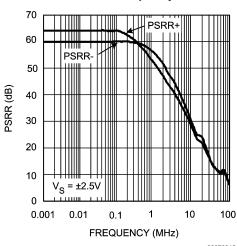
Typical Performance Characteristics $A_V = 2$, $R_F = 1200\Omega$, $R_L = 100\Omega$, unless otherwise

specified. (Continued)

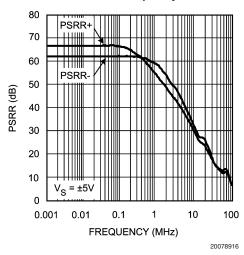


Suggested R_{OUT} vs. C_L

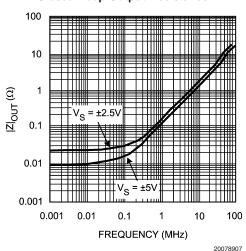




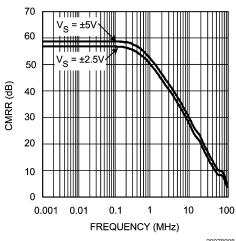




Closed Loop Output Resistance

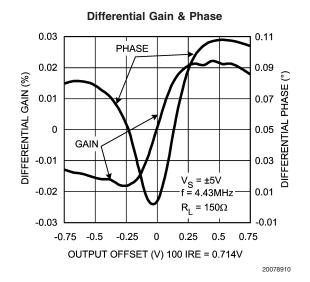


CMRR vs. Frequency

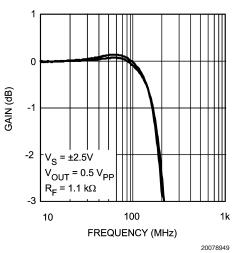


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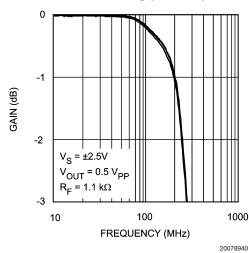
Typical Performance Characteristics $A_V = 2$, $R_F = 1200\Omega$, $R_L = 100\Omega$, unless otherwise specified. (Continued)



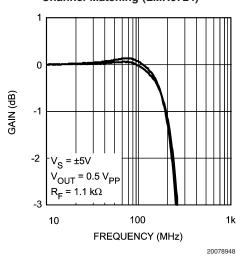
Channel Matching (LMH6724)



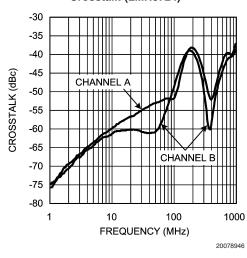
Channel Matching (LMH6725)



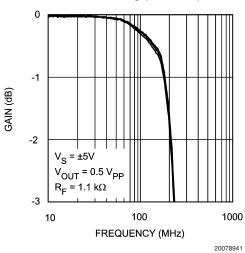
Channel Matching (LMH6724)



Crosstalk (LMH6724)

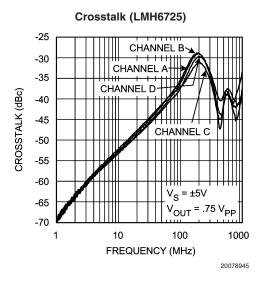


Channel Matching (LMH6725)



Typical Performance Characteristics A_V = 2, R_F = 1200 Ω , R_L = 100 Ω , unless otherwise

specified. (Continued)



Application Section

GENERAL INFORMATION

The LMH6723/LMH6724/LMH6725 is a high speed current feedback amplifier manufactured on National Semiconductor's VIP10 (Vertically Integrated PNP) complimentary bipolar process. LMH6723/LMH6724/LMH6725 offers a unique combination of high speed and low quiescent supply current making it suitable for a wide range of battery powered and portable applications that require high performance. This amplifier can operate from 4.5V to 12V nominal supply voltages and draws only 1 mA of quiescent supply current at 10V supplies (±5V typically). The LMH6723/LMH6724/LMH6725 has no internal ground reference so single or split supply configurations are both equally useful.

EVALUATION BOARDS

National Semiconductor provides the following evaluation boards as a guide for high frequency layout and as an aid in device testing and characterization. Many of the datasheet plots were measured with these boards.

Device	Package	Board Part #
LMH6723MA	SOIC-8	CLC730227
LMH6723MF	SOT-23	CLC730216
LMH6724MA	SOIC-8	CLC730036
LMH6725MA	SOIC-14	CLC730231

These evaluation boards can be shipped when a device sample request is placed with National Semiconductor.

FEEDBACK RESISTOR SELECTION

One of the key benefits of a current feedback operational amplifier is the ability to maintain optimum frequency response independent of gain by using appropriate values for the feedback resistor (R $_{\rm F}$). The Electrical Characteristics and Typical Performance plots were generated with an R $_{\rm F}$ of 1200 Ω , a gain of +2V/V and ±5V or ±2.5V power supplies (unless otherwise specified). Generally, lowering R $_{\rm F}$ from it's recommended value will peak the frequency response and extend the bandwidth; however, increasing the value of R $_{\rm F}$

will cause the frequency response to roll off faster. Reducing the value of $R_{\rm F}$ too far below it's recommended value will cause overshoot, ringing and, eventually, oscillation.

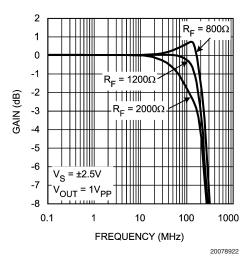


FIGURE 1. Frequency Response vs. R_F

Figure 1 shows the LMH6723/LMH6724/LMH6725's frequency response as $R_{\rm F}$ is varied ($R_{\rm L}=100\Omega,\,A_{\rm V}=+2).$ This plot shows that an $R_{\rm F}$ of 800Ω results in peaking. An $R_{\rm F}$ of 1200Ω gives near maximal bandwidth and gain flatness with good stability. Since each application is slightly different it is worth some experimentation to find the optimal $R_{\rm F}$ for a given circuit. In general a value of $R_{\rm F}$ that produces $^{\sim}0.1$ dB of peaking is the best compromise between stability and maximal bandwidth. Note that it is not possible to use a current feedback amplifier with the output shorted directly to the inverting input. The buffer configuration of the LMH6723/LMH6724/LMH6725 requires a 2000Ω feedback resistor for stable operation. For other gains see the charts " $R_{\rm F}$ vs. Non

Application Section (Continued)

Inverting Gain" and " R_F vs. Inverting Gain". These charts provide a good place to start when selecting the best feedback resistor value for a variety of gain settings.

For more information see Application Note OA-13 which describes the relationship between R_{F} and closed-loop frequency response for current feedback operational amplifiers. The value for the inverting input impedance for the LMH6723/LMH6724/LMH6725 is approximately $500\Omega.$ The LMH6723/LMH6724/LMH6725 is designed for optimum performance at gains of +1 to +5V/V and -1 to -4V/V. Higher gain configurations are still useful; however, the bandwidth will fall as gain is increased, much like a typical voltage feedback amplifier.

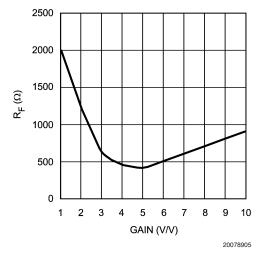


FIGURE 2. RF vs. Non-Inverting Gain

Figure 2 and Figure 3 show the value of R_F versus gain. A higher R_F is required at higher gains to keep R_G from decreasing too far below the input impedance of the inverting input. This limitation applies to both inverting and non-inverting configurations. For the LMH6723/LMH6724/LMH6725 the input resistance of the inverting input is approximately 500Ω and 100Ω is a practical lower limit for R_G. The LMH6723/LMH6724/LMH6725 begins to operate in a gain bandwidth limited fashion in the region where R_F must be increased for higher gains. Note that the amplifier will operate with R_G values well below 100Ω; however, results will be substantially different than predicted from ideal models. In particular, the voltage potential between the Inverting and Non-Inverting inputs cannot be expected to remain small.

For inverting configurations the impedance seen by the source is R_G II R_T . For most sources this limits the maximum inverting gain since R_F is determined by the desired gain as shown in Figure 3. The value of R_G is then $R_F/Gain$. Thus for an inverting gain of -4 V/V the input impedance is equal to $100\Omega.$ Using a termination resistor, this can be brought down to match a 50Ω or 75Ω source; however, a 150Ω source cannot be matched without a severe compromise in $R_F.$

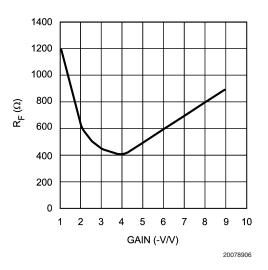


FIGURE 3. R_F vs. Inverting Gain

ACTIVE FILTERS

When using any current feedback operational amplifier as an active filter it is necessary to be careful using reactive components in the feedback loop. Reducing the feedback impedance, especially at higher frequencies, will almost certainly cause stability problems. Likewise capacitance on the inverting input should be avoided. See Application Notes OA-7 and OA-26 for more information on Active Filter applications for Current Feedback Op Amps.

When using the LMH6723/LMH6724/LMH6725 as a low-pass filter the value of R_{F} can be substantially reduced from the value recommended in the R_{F} vs. Gain charts. The benefit of reducing R_{F} is increased gain at higher frequencies, which improves attenuation in the stop band. Stability problems are avoided because in the stop band additional device bandwidth is used to cancel the input signal rather than amplify it. The benefit of this change depends on the particulars of the circuit design. With a high pass filter configuration reducing R_{F} will likely result in device instability and is not recommended.

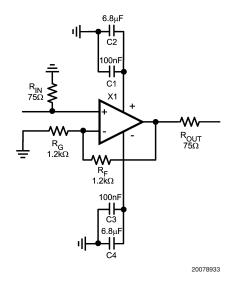


FIGURE 4. Typical Application with Suggested Supply Bypassing

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Application Section (Continued)

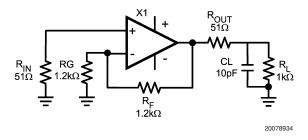


FIGURE 5. Decoupling Capacitive Loads

DRIVING CAPACITIVE LOADS

Capacitive output loading applications will benefit from the use of a series output resistor as shown in Figure 5. The charts "Suggested $R_{\rm OUT}$ vs. Cap Load" give a recommended value for selecting a series output resistor for mitigating capacitive loads. The values suggested in the charts are selected for .5 dB or less of peaking in the frequency response. This gives a good compromise between settling time and bandwidth. For applications where maximum frequency response is needed and some peaking is tolerable, the value of $R_{\rm OUT}$ can be reduced slightly from the recommended values.

There will be amplitude lost in the series resistor unless the gain is adjusted to compensate; this effect is most noticeable with heavy loads ($R_L < 150\Omega$).

An alternative approach is to place R_{OUT} inside the feedback loop as shown in *Figure 6*. This will preserve gain accuracy, but will still limit maximum output voltage swing.

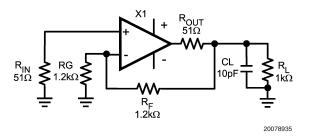


FIGURE 6. Series Output Resistor inside feedback loop

INVERTING INPUT PARASITIC CAPACITANCE

Parasitic capacitance is any capacitance in a circuit that was not intentionally added. It is produced through electrical interaction between conductors and can be reduced but never entirely eliminated. Most parasitic capacitances that cause problems are related to board layout or lack of termination on transmission lines. Please see the section on Layout Considerations for hints on reducing problems due to parasitic capacitances on board traces. Transmission lines should be terminated in their characteristic impedance at both ends.

High speed amplifiers are sensitive to capacitance between the inverting input and ground or power supplies. This shows up as gain peaking at high frequency. The capacitor raises device gain at high frequencies by making $R_{\rm G}$ appear smaller. Capacitive output loading will exaggerate this effect.

One possible remedy for this effect is to slightly increase the value of the feedback (and gain set) resistor. This will tend to offset the high frequency gain peaking while leaving other parameters relatively unchanged. If the device has a capacitive load as well as inverting input capacitance, using a series output resistor as described in the section on "Driving Capacitive Loads" will help.

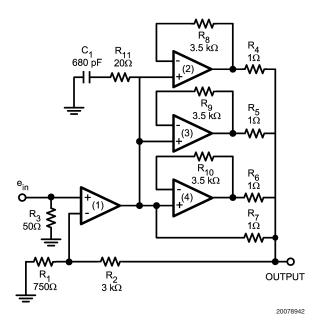


FIGURE 7. High Output Current Composite Amplifier

When higher currents are required than a single amplifier can provide, the circuit of Figure 7 can be used. Although the example circuit was intended for the LMH6725 quad op amp, higher thermal efficiency can be obtained by using four separate SOIC op amps. Careful attention to a few key components will optimize performance from this circuit. The first thing to note is that the buffers need slightly higher value feedback resistors than if the amplifiers were individually configured. As well, R_{11} and C_1 provide mid circuit frequency compensation to further improve stability. The composite amplifier has approximately twice the phase delay of a single circuit. The larger values of $R_8,\ R_9$ and $R_{10},\ as$ well as the high frequency attenuation provided by C_1 and $R_{11},\ ensure$ that the circuit does not oscillate.

Resistors R_4 , R_5 , R_6 , and R_7 are necessary to ensure even current distribution between the amplifiers. Since they are inside the feedback loop they have no effect on the gain of the circuit. The circuit shown in *Figure 7* has a gain of 5. The frequency response of this circuit is shown in *Figure 8*.

Application Section (Continued)

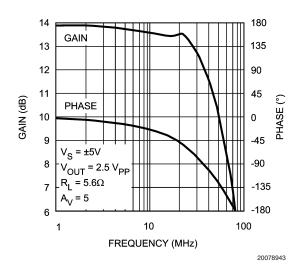


FIGURE 8. Composite Amplifier Frequency Response

LAYOUT CONSIDERATIONS

Whenever questions about layout arise, use the evaluation board as a guide. Evaluation boards are shipped with sample requests.

To reduce parasitic capacitances ground and power planes should be removed near the input and output pins. Components in the feedback loop should be placed as close to the device as possible. For long signal paths controlled impedance lines should be used, along with impedance matching at both ends.

Bypass capacitors should be placed as close to the device as possible. Bypass capacitors from each rail to ground are applied in pairs. The larger electrolytic bypass capacitors can be located anywhere on the board; however, the smaller ceramic capacitors should be placed as close to the device as possible.

VIDEO PERFORMANCE

The LMH6723/LMH6724/LMH6725 has been designed to provide good performance with both PAL and NTSC composite video signals. The LMH6723/LMH6724/LMH6725 is specified for PAL signals. Typically, NTSC performance is marginally better due to the lower frequency content of the signal. Performance degrades as the loading is increased;

therefore, best performance will be obtained with back terminated loads. The back termination reduces reflections from the transmission line and effectively masks transmission line and other parasitic capacitances from the amplifier output stage. Figure 4 shows a typical configuration for driving a 75Ω cable. The amplifier is configured for a gain of 2 to make up for the 6dB of loss in $R_{\rm OUT}$.

SINGLE 5V SUPPLY VIDEO

With a 5V supply the LMH6723/LMH6724/LMH6725 is able to handle a composite NTSC video signal, provided that the signal is AC coupled and level shifted so that the signal is centered around $V_{\rm CC}/2$.

POWER DISSIPATION

Follow these steps to determine the maximum power dissipation for the LMH6723/LMH6724/LMH6725:

- 1. Calculate the quiescent (no-load) power: $P_{AMP} = I_{CC}^{*}$ (V_{S}) $V_{S} = V^{+} V^{-}$
- 2. Calculate the RMS power dissipated in the output stage: P_D (rms) = rms ($(V_S-V_{OUT})^*I_{OUT}$) where V_{OUT} and I_{OUT} are the voltage and current across the external load and V_S is the total supply current.
- 3. Calculate the total RMS power: $P_T = P_{AMP} + P_D$

The maximum power that the LMH6723/LMH6724/LMH6725 package can dissipate at a given temperature can be derived with the following equation:

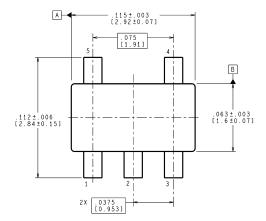
 $P_{MAX}=(150^{o}$ - $T_{AMB})/$ $\theta_{JA},$ where $T_{AMB}=$ Ambient temperature (°C) and $\theta_{JA}=$ Thermal resistance, from junction to ambient, for a given package (°C/W). For the SOIC-8 package θ_{JA} is 166°C/W and for the SOT it is 230°C/W. The SOIC-14 has a θ_{JA} of 130°C/W. The TSSOP-14 has a θ_{JA} of 160°C/W.

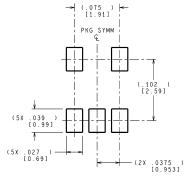
ESD PROTECTION

The LMH6723/LMH6724/LMH6725 is protected against electrostatic discharge (ESD) on all pins. The LMH6723/LMH6725 will survive 2000V Human Body Model or 200V Machine Model events.

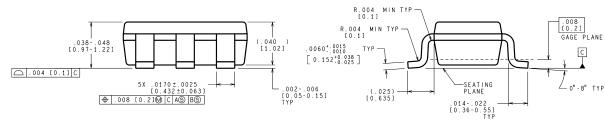
Under closed loop operation the ESD diodes have no effect on circuit performance. There are occasions, however, when the ESD diodes will be evident. If the LMH6723/LMH6724/LMH6725 is driven into a slewing condition the ESD diodes will clamp large differential voltages until the feedback loop restores closed loop operation. Also, if the device is powered down and a large input signal is applied, the ESD diodes will conduct.

Physical Dimensions inches (millimeters) unless otherwise noted





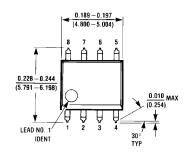


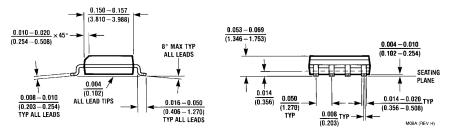


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MF05A (Rev B)

5-Pin SOT23 **NS Product Number MF05A**

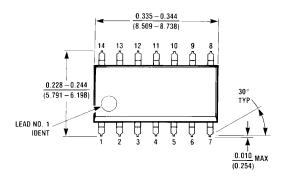


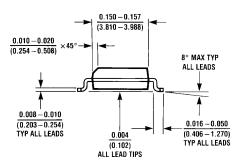


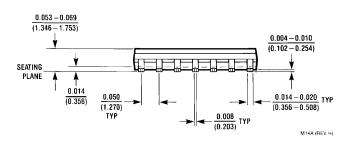
8-Pin SOIC **NS Product Number M08A**

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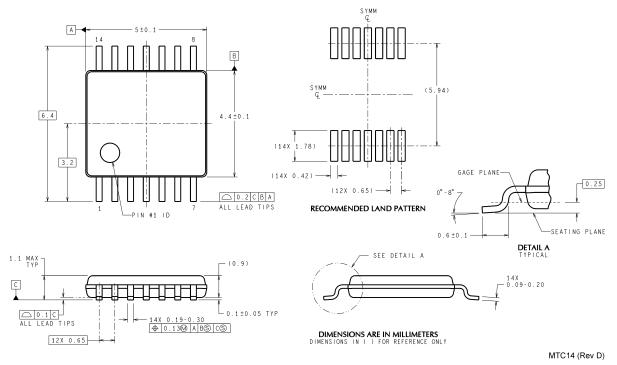
Physical Dimensions inches (millimeters) unless otherwise noted (Continued)







14-Pin SOIC NS Product Number M14A



14-Pin TSSOP NS Product Number MTC14

Notes

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